

Form PTO-1449 (REV. 8-83)	US Dept. of Commerce PATENT & TRADEMARK OFFICE	ATTY DOCKET NO. 118490	APPLICATION NO. New U.S. Patent Application 10/786,151
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		APPLICANT Mitsutoshi MIYASAKA	
		FILING DATE February 26, 2004	2815

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS

FOREIGN PATENT DOCUMENTS						
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS
EO	1	JP A 2003-289040 w/ abst & trans	10/10/2003	Japan		
EO	2	JP A 9-172183 w/ abst & trans	06/30/1997	Japan		

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)		
EO	3	"TBD: Single Crystal Thin Film Transistors" Webpage. <i>IBM Technical Disclosure Bulletin</i> August 1993, pp. 257-258 http://www.delphion.com/tbds/tbd?&order=93A+61960
EO	4	Ishihara, Ryoichi et al. "Advanced Excimer-Laser Crystallization Techniques of Si Thin-Film for Location Control of Large Grain on Glass." <i>Flat Panel Display Technology and Display Metrology II</i> Proceedings of SPIE Vol. 4295. 2001, pp. 14-23

EXAMINER Edgardo Lity	DATE CONSIDERED 8/9/05
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	